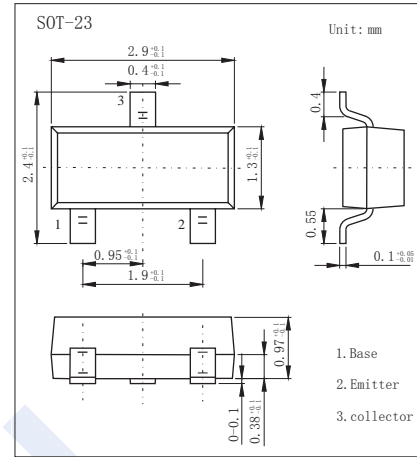


PNP Transistors

2KB4003

■ Features

- Ideally suited for automatic insertion
- Epitaxial planar die construction
- Complementary NPN type available(2KD3003)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-50	V
Collector - Emitter Voltage	V_{CE0}	-45	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-0.5	A
Power Dissipation	P_D	0.3	W
Thermal Resistance, Junction- to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -10\text{mA}, I_B = 0$	-45			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -45\text{V}, I_E = 0$			-0.1	μA
Collector- emitter cut-off current	I_{CE0}	$V_{CE} = -40\text{V}, I_B = 0$			-0.2	
Emitter cut-off current	I_{EB0}	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1.2	
DC current gain	$h_{fe}(1)$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	250		630	
	$h_{fe}(2)$	$V_{CE} = -1\text{V}, I_C = -500\text{mA}$	40			
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$	100			MHz

■ Marking

Marking	2E
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■ Typical Characteristics

